Electronic Supplementary Information for

Continuous wave Pumped Nanolasers of Single-mode in Inorganic Perovskites with Robust Stability and High Quantum Yield

Li Jiang, ^a Renming Liu, ^a Rongling Su, ^a Ying Yu, ^a Haofei Xu, ^a Yuming Wei, ^a Zhang-Kai Zhou, ^{*} ^a and Xuehua Wang ^a

^a State Key Laboratory of Optoelectronic Materials and Technologies, School of Physics, Sun Yat-sen University, Guangzhou 510275, China. L. Jiang and R. Liu contributed equally to this work.

*Correspondence and requests for materials should be addressed to Z.K.Z. (Email: zhouzhk@mail.sysu.edu.cn)



Fig. S1 Scheme of the beaker used for the growth of $CsPbX_3$ NWs using the gas-liquid transfer recrystallization method



Fig. S2 The SEM photographs of $CsPbBr_3$ crystals from different volume of IPA (in a 100-mL beaker), (a) 50 mL, (b) 10 mL.



Fig. S3 The SEM photographs of $CsPbBr_3$ crystals from different vapor/atmosphere: (a) isopropanol, (b) n-propanol, (c) butyl alcohol, (d) cyclohexane, (e) dichloromethane, (f) ethanol, (g) Air, (h)nitrogen.



Fig. S4 (a-d) The morphological features (SEM images) of CsPbBr₃ NWs with diferent length. The length of the nanowires can be adjusted from 2~10μm, by controlling the precursor concentration. (e) A representative EDS spectrum of a single CsPbBr₃ NW on a silicon substrate. The inset shows quantitative elemental analysis of the corresponding EDS. (f) A representative EDS spectrum of a single CsPbCl₃ NW on a silicon substrate. The inset shows quantitative elemental analysis of the corresponding EDS. (g) A representative EDS spectrum of a single CsPbl₃ NW on a silicon substrate. The inset shows quantitative elemental analysis and SEM image of the corresponding EDS. (g) A representative EDS spectrum of a single CsPbl₃ NW on a silicon substrate. The inset shows quantitative elemental analysis and SEM image of the corresponding EDS, demonstrating Cs, Pb and X (Cl, Br, I) components with a quantified ration of 1:1:3.



Fig. S5 More details about the morphological and cross section of CsPbBr₃ NWs



Fig. S6 Different lasing behaviors of a single perovskite nanowire. (a) single mode, (b) double-mode and (c) multi-mode. The undefined scale bar indicates $1 \mu m$.



Fig. S7 Femtosecond-pumped PL intensities with below (black line) and above P_{th} (red line) from a single CsPbBr₃ NW, showing a linewidth of 0.26 nm..



Fig. S8 Low temperature measurements of single nanowire. (a) Optical micrographs; (b) and the corresponding SEM image, inset: the magnification SEM images; (c) Schematic sketch of experimental system configuration for lasing measurements on a single nanowire at low temperature. By comparing the optical micrograph (a) and its corresponding SEM image (b), one can indentify a specific nanowire that has been measured (marked by red cycle). The well-controlled laser beams (laser spot, the diameter is ~2 μ m) can also be clearly observed in the optical image (a), which demonstrates the excitation of a single nanwire.



Fig. S9 The linewidth of $CsPbBr_3$ NWs lasing with single mode (a), double-mode (b) and multi-mode (c). (d) The corresponding statistical linewidth of lasing spectra.



Fig. S10 Multi-mode lasing actions of a single CsPbBr₃ NW after reserving in clean room for over one year. (a) The fluence-dependent of lasing spectra from a single CsPbBr₃ NW with multi-mode lasing. (b) The fluence-dependent of the single mode lasing intensity showing a threshold of 1.50 nW.



Fig. S11 Lasing reactions of CsPbBr₃ NW with poor crystallization. (a) XRD results and a typical SEM image of a CsPbBr₃ NW with poor crystallization. Such NWs are synthesized under ~30 °C, which is ~8 °C higher than the suitable temperature. (b) Typical PL spectra and the fluence-dependent of lasing spectra from the single CsPbBr₃ NW. T the lasing threshold and linewidth are repectively 300 times higher and 10 times broader than those of the CsPbBr₃ NWs reported in the maintext. (c) The PL spectrum of the CsPbBr₃ NW with poor crystallization after one year preservation. No lasing action can be observed. In (b) and (c) the sample was pumped by CW laser, and the measurement temperature was 4 K.

Р	A	T ₁ (ns)	T ₂ (ns)	Bn	k _{lasing} n	Note QY(%)	Lasing QY (%)
0.5P _{th}	0.3482×10 ⁹	2.45		0.0599×10 ⁹		15	
0.8P _{th}	0.3482×10 ⁹	2.25		0.0962×10 ⁹		22	
1.1P _{th}	0.3482×10 ⁹	0.59	2.15	0.1169×10 ⁹	0.4260×10 ⁹	61	48
2.0 P _{th}	0.3482×10 ⁹	0.57	2.05	0.1396×10 ⁹	0.5020×10 ⁹	65	51
3.0P _{th}	0.3482×10 ⁹	0.49	1.82	0.2012×10 ⁹	0.7473×10 ⁹	73	58

Table. S1 Estimated Quantum yields (QY) and lasing QY of a single CsPbBr₃ NWs (the data are analyzed from Fig. 3a.

(1)

Note: $QY = \frac{\text{radiative rate}}{\text{total rate}} = \frac{Bn + k_{\text{lasing}}n}{A + Bn + k_{\text{lasing}}n}$

Lasing QY = $\frac{\text{lasing rate}}{\text{total rate}} = \frac{k_{\text{lasing}}n}{A + Bn + k_{\text{lasing}}n}$ (2)